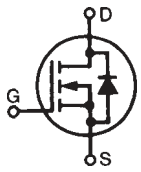
IXYS

Polar™ HiPerFET™ Power MOSFET

IXFL82N60P

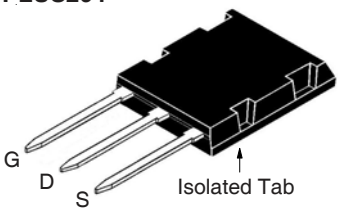
V_{DSS} = 600V
I_{D25} = 55A
$R_{DS(on)}$ ≤ 78mΩ
t_{rr} ≤ 200ns

(Electrically Isolated Tab)



N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Rectifier

ISOPLUS264



G = Gate D = Drain
S = Source

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	600	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	600	V
V_{GSS}	Continuous	±30	V
V_{GSM}	Transient	±40	V
I_{D25}	T_C = 25°C	55	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	200	A
I_A	T_C = 25°C	82	A
E_{AS}	T_C = 25°C	5	J
dv/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$	20	V/ns
P_D	T_C = 25°C	625	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	Plastic Body for 10s	260	°C
F_C	Mounting Force	40..120 / 9..27	N/lb.
V_{ISOL}	50/60 Hz, RMS t = 1 min	2500	V~
	$I_{ISOL} \le$ 1 mA t = 1 s	3000	V~
Weight		8	g

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 3mA	600			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 8mA	3.0		5.0	V
I_{GSS}	V_{GS} = ±30V, V_{DS} = 0V			±200	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0V			25	μA
	T_J = 125°C			1	mA
$R_{DS(on)}$	V_{GS} = 10V, I_D = 41A, Note 1			78	mΩ

Features

- Silicon Chip on Direct-Copper-Bond Substrate
  - High Power Dissipation
  - Isolated Mounting Surface
  - 2500V~ Electrical Isolation
- Avalanche Rated
- Low Package Inductance
- Fast Intrinsic Rectifier
- Low $R_{DS(on)}$ and Q_G

Advantages

- Easy to Mount
- Space Savings

AApplications

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- AC Motor Control
- High Speed Power Switching Appliccation

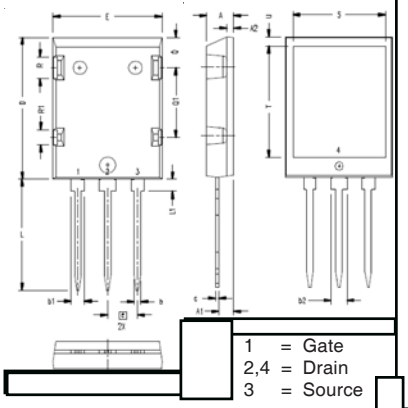
Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 20V, I_D = 41A, Note 1	50	80		S
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		23		nF
C_{oss}			1490		pF
C_{rss}			200		pF
$t_{d(on)}$	**Resistive Switching Times**		28		ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 41A		23		ns
$t_{d(off)}$	R_G = 1Ω (External)		79		ns
t_f			24		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 41A		240		nC
Q_{gs}			96		nC
Q_{gd}			67		nC
R_{thJC}				0.20	°C/W
R_{thCS}			0.15		°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			100	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			200	A
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			1.5	V
t_{rr}	I_F = 25A, -di/dt = 100A/μs			200	ns
Q_{RM}	V_R = 100V, V_{GS} = 0V		0.6		μC
I_{RM}			6.0		A

Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

ISOPLUS264 (IXFL) OUTLINE



1 = Gate
2,4 = Drain
3 = Source

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.190	.205	4.83	5.21
A1	.102	.118	2.59	3.00
A2	.046	.055	1.17	1.40
b	.045	.055	1.14	1.40
b1	.087	.102	2.21	2.59
b2	.111	.126	2.82	3.20
c	.020	.029	0.51	0.74
D	1.020	1.040	25.91	26.42
E	.770	.799	19.56	20.29
e	.215 BSC		5.46 BSC	
L	.780	.820	19.81	20.83
L1	.080	.102	2.03	2.59
Q	.210	.235	5.33	5.97
Q1	.490	.513	12.45	13.03
R	.150	.180	3.81	4.57
R1	.100	.130	2.54	3.30
S	.668	.690	16.97	17.53
T	.801	.821	20.34	20.85
U	.065	.080	1.65	2.03

Fig. 1. Output Characteristics @ T_J = 25°C

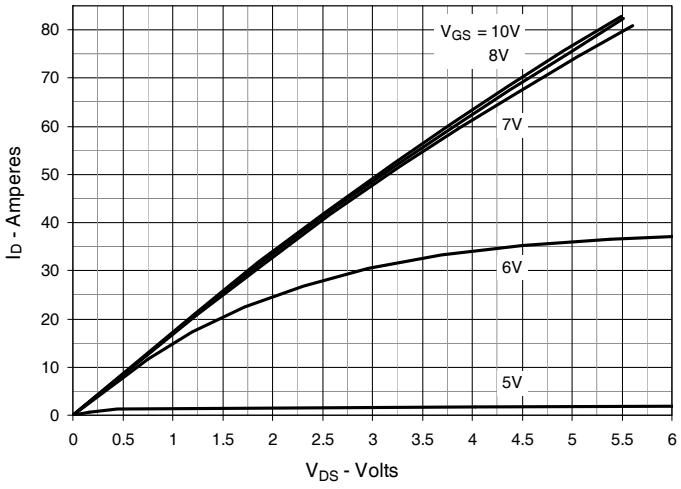


Fig. 2. Extended Output Characteristics @ T_J = 25°C

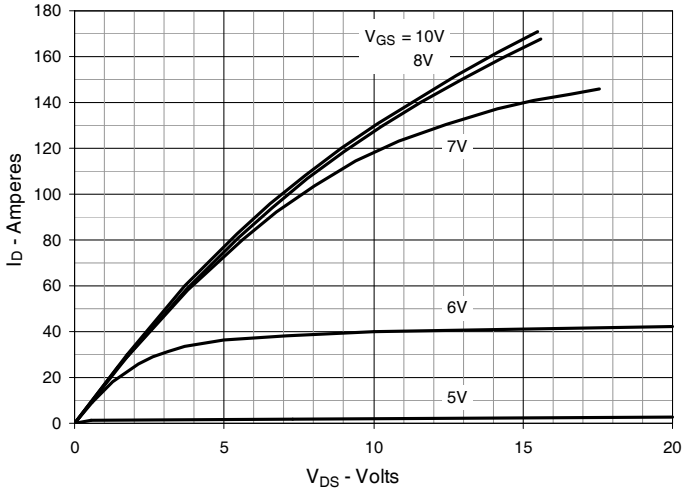


Fig. 3. Output Characteristics @ T_J = 125°C

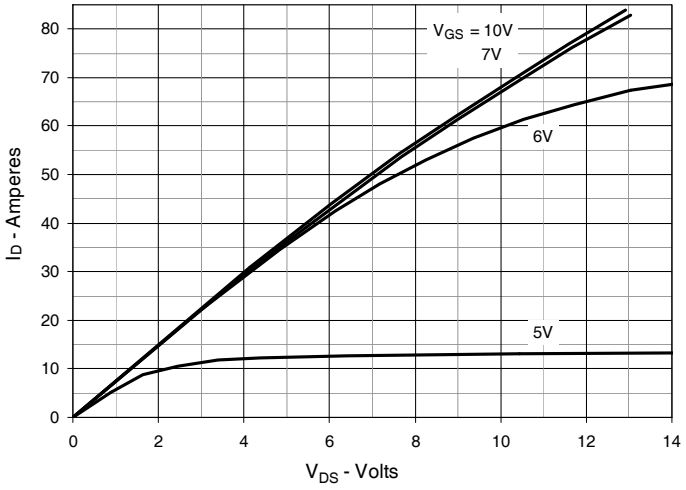


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 41A Value vs. Junction Temperature

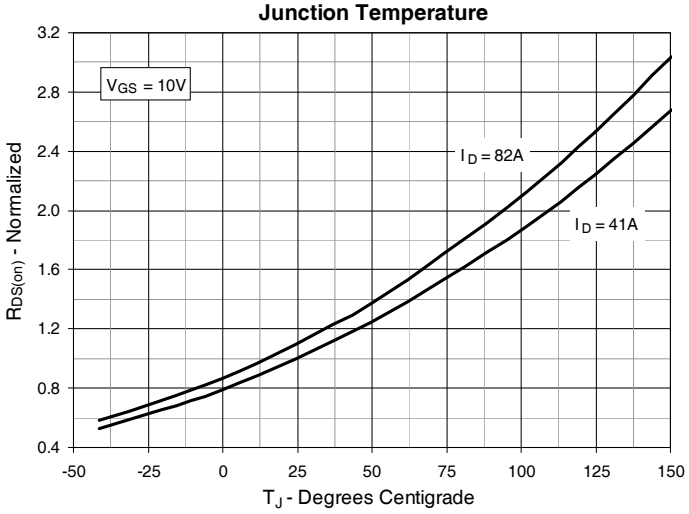


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 41A Value vs. Drain Current

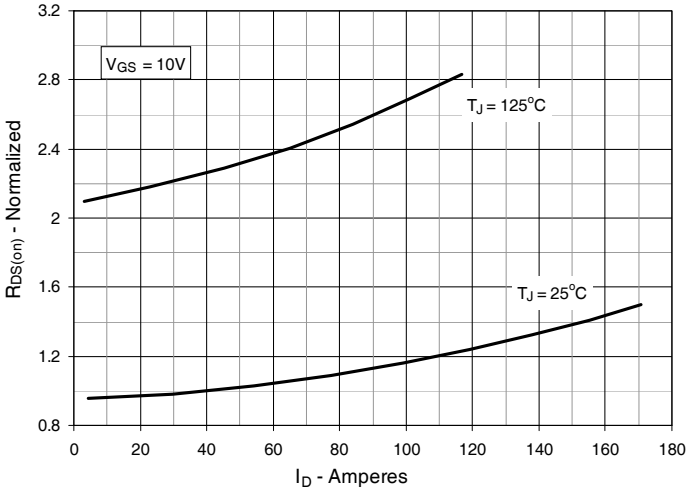


Fig. 6. Maximum Drain Current vs. Case Temperature

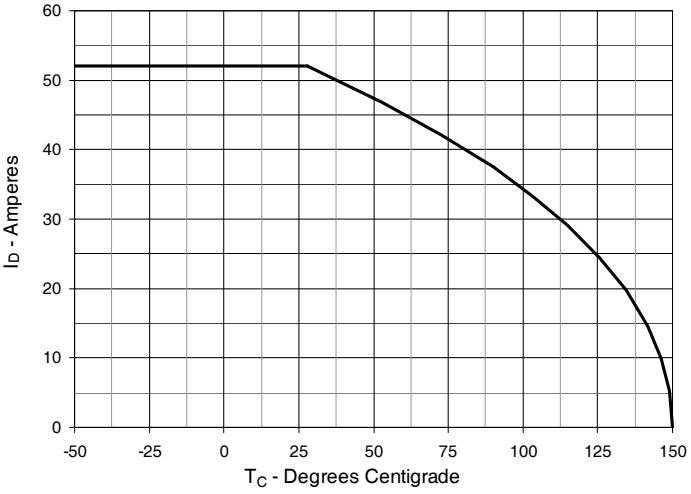


Fig. 7. Input Admittance

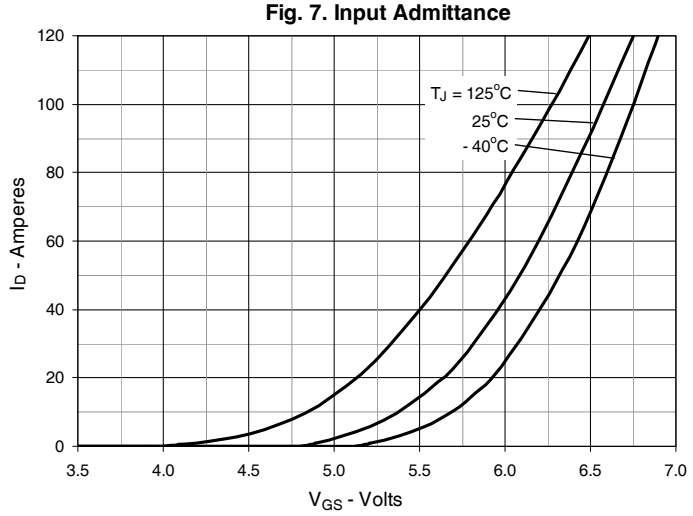


Fig. 8. Transconductance

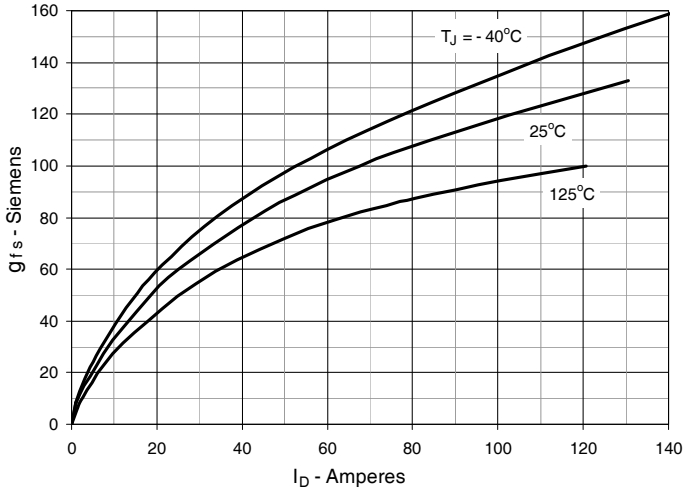


Fig. 9. Forward Voltage Drop of Intrinsic Diode

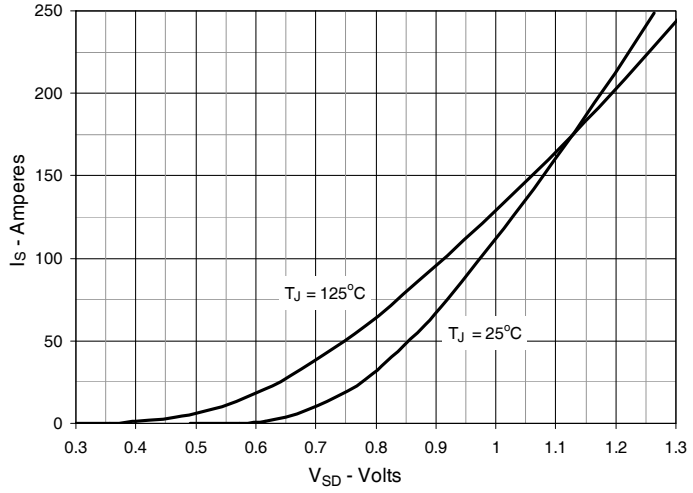


Fig. 10. Gate Charge

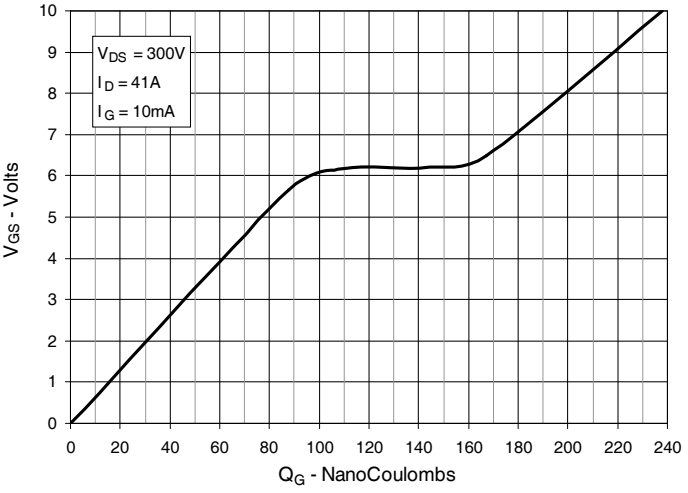


Fig. 11. Capacitance

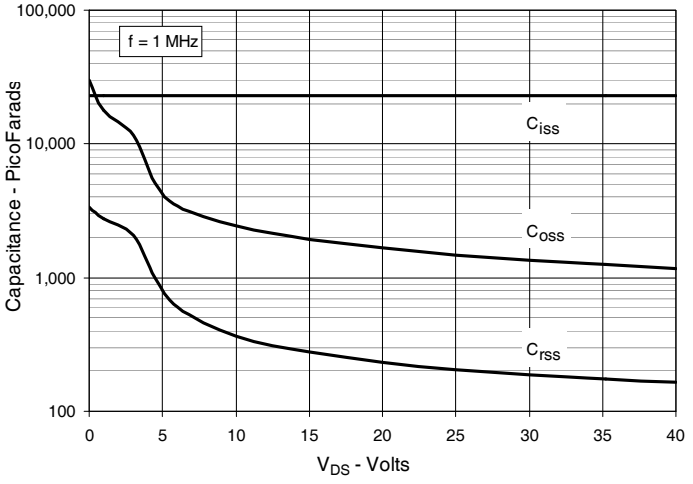


Fig. 12. Forward-Bias Safe Operating Area

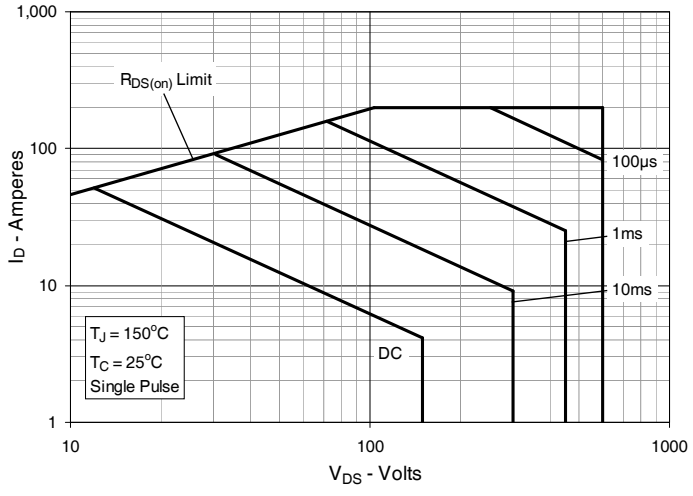


Fig. 13. Maximum Transient Thermal Impedance